

MITSUBISHI LASER DIODES
ML6XX15 SERIES

AlGaAs LASER DIODES

TYPE
NAME

ML60115R

DISCRIPTION

ML6XX15 is a high power AlGaAs semiconductor laser diodes which provides a stable, single transverse mode oscillation with emission wavelength of 785nm and standard light output of 30mW.

ML6XX15 is produced by the MOCVD crystal growth method which is excellent in mass production and characteristics uniformity. This is a high - performance, highly reliable, and long life semiconductor laser.

FEATURES

- Output 30mW (CW) 40mW (pulse)
- Short astigmatic distance
- Built - in monitor photodiode
- MQW* active layer
- *Multiple Quantum Well

APPLICATION

Optical disc memory (rewritable, write once)

ABSOLUTE MAXIMUM RATINGS (Note 1)

| Symbol | Parameter | Conditions | Ratings | Unit |
|--------|-------------------------------|------------|---------------|------|
| | | | | |
| Po | Light output power | — | CW | 35 |
| | | | Pulse (Note2) | 45 |
| VRL | Reverse voltage (Laser diode) | — | 2 | V |
| VRD | Reverse voltage (photodiode) | — | 30 | V |
| IFD | Forward current (photodiode) | — | 10 | mA |
| Tc | Case temperature | — | -40~+60 | °C |
| Tstg | Storage temperature | — | -55~+100 | °C |

Note 1 : Duty less than 50%, pulse width less than 1 μs

2: The maximum rating means the limitation over which the laser should not be operated even instant time, and this does not mean the guarantee of its lifetime. As for the reliavility, please refer to the reliability report from Mitsubishi Semiconductor Quality Assurance Department.

ELECTRICAL/OPTICAL CHARACTERISTICS (Tc = 25°C)

| Symbol | Parameter | Test conditions | Limits | | | Unit |
|--------|--|---|--------|------|------|-------|
| | | | Min. | Typ. | Max. | |
| Ith | Threshold current | CW | — | 35 | 55 | mA |
| IOP | Operating current | CW, Po = 30mW | — | 90 | 110 | mA |
| VOP | Operating voltage | CW, Po = 30mW | — | 2.0 | 2.5 | V |
| η | Slope efficiency | CW, Po = 30mW | 0.40 | 0.55 | 0.75 | mW/mA |
| λP | Peak Wavelength | CW, Po = 30mW | 770 | 785 | 800 | nm |
| θ// | Beam divergence angle (parallel) | CW, Po = 30mW | 8 | 10 | 13 | deg. |
| θ⊥ | Beam divergence angle (perpendicular) | CW, Po = 30mW | 22 | 25 | 28 | deg. |
| Im | Monitoring output current (photodiode) | CW, Po = 30mW, VRD = 1V, RL = 10 Ω (Note 3) | — | 0.4 | — | mA |
| ID | Dark current (photodiode) | VRD = 10V | — | — | 0.5 | μA |
| Ct | Capacitance (photodiode) | VRD = 5V, f = 1MHz | — | 7 | — | pF |

Note 3 : RL = the load resistance of photodiode

MITSUBISHI LASER DIODES
ML6XX15 SERIES

AlGaAs LASER DIODES

TYPICAL CHARACTERISTICS

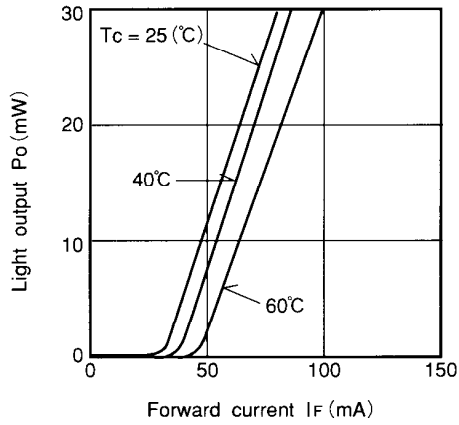


Fig. 1 Light output vs. forward current

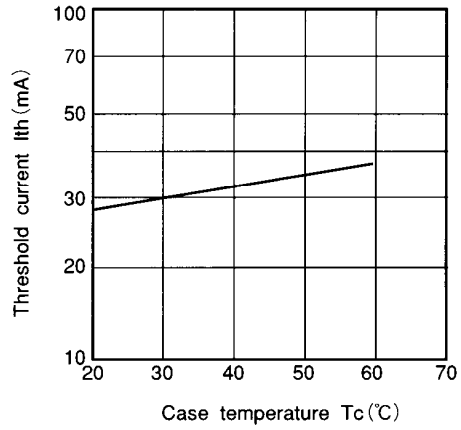


Fig. 2 Temperature dependence of threshold current

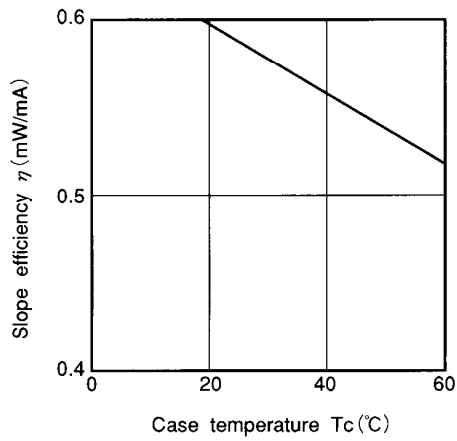


Fig. 3 Case temperature dependence of slope efficiency

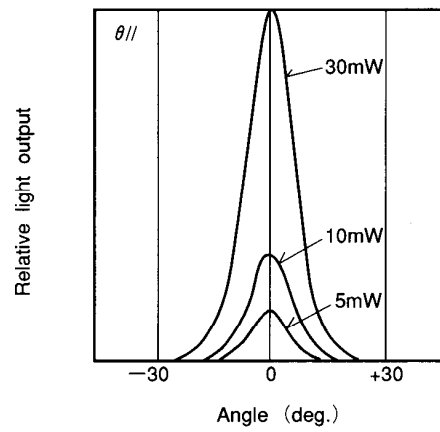


Fig. 4 Far field pattern $\theta_{//}$

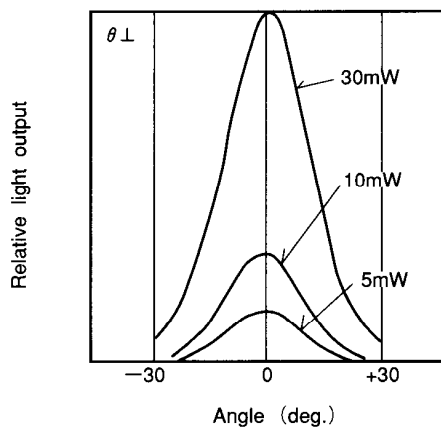


Fig. 5 Far field pattern θ_{\perp}